

SOT-23 Plastic-Encapsulate Transistors

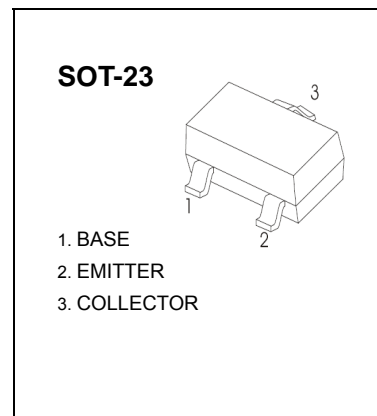
S9015 TRANSISTOR (PNP)

FEATURES

- Complementary to S9014

MARKING: M6

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)



Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.1	A
P _C	Collector Power Dissipation	0.2	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E = 0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B = 0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -5V, I _C = -1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B = -10mA			-1	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f = 30MHz	150			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-450	450-1000

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Static Characteristic

